

CLAIMS:

1. A semiconductor processor system comprising:

a process chamber adapted to process at least one semiconductor workpiece using a process fluid;

a connection coupled with the process chamber and configured to receive the process fluid;

a sensor coupled with the connection and configured to output a signal indicative of the process fluid; and

a control system coupled with the sensor and configured to control at least one operation of the semiconductor processor system responsive to the signal.

2. The system according to claim 1 wherein the connection comprises a connection of a sampling system configured to provide the process fluid in a substantially static state.

3. The system according to claim 2 wherein the control system is configured to compare the substantially static process fluid with a signature to determine at least one characteristic of the process fluid.

4. The system according to claim 3 wherein the control system is configured to control a flow rate of the process fluid into the process chamber responsive to the comparison.

1 5. The system according to claim 4 wherein the control system
2 is configured to halt processing within the process chamber responsive
3 to the comparison.

4
5 6. The system according to claim 1 wherein the sensor is
6 configured to monitor turbidity of the process fluid.

7
8 7. The system according to claim 1 wherein the connection is
9 adapted to couple with a process fluid supply and is configured to
10 supply process fluid from the process fluid supply to the process
11 chamber.

12
13 8. The system according to claim 1 wherein the connection
14 comprises a drain coupled with the process chamber.

15
16 9. The system according to claim 1 wherein the process
17 chamber comprises a pad adapted to process the at least one
18 semiconductor workpiece and the connection is configured to extract
19 process fluid from the pad.

20
21 10. The system according to claim 1 wherein the sensor is
22 configured to output a signal indicative of accumulation of particulate
23 matter within the connection.

24

1 11. The system according to claim 1 wherein the control system
2 is configured to process the signal to monitor processing of the at least
3 one semiconductor workpiece within the process chamber.

4
5 12. The system according to claim 1 further comprising a flush
6 system coupled with the connection and configured to selectively flush
7 the connection.

8
9 13. The system according to claim 12 wherein the flush system
10 is configured to flush the connection with at least one of the process
11 fluid and a rinse fluid.

12
13 14. The system according to claim 12 wherein the flush system
14 is configured to flush the connection responsive to control from the
15 control system.

16
17 15. The system according to claim 1 further comprising a mixing
18 system configured to mix plural components of the process fluid and the
19 control system is configured to control the mixing system.

20
21 16. The system according to claim 1 further comprising a
22 storage device configured to store historical data corresponding to the
23 process fluid.

24

1 17. The system according to claim 1 wherein the process
2 chamber comprises a process chamber of a chemical-mechanical polishing
3 processor.

4
5 18. A semiconductor processor system comprising:
6 a process chamber adapted to process at least one semiconductor
7 workpiece using a process fluid;

8 a connection coupled with the process chamber and configured to
9 transport the process fluid;

10 a sampling system coupled with the connection and configured to
11 receive a sample of the process fluid;

12 a sensor coupled with the sampling system and configured to
13 output a signal indicative of the sample of the process fluid; and

14 a control system coupled with the sensor and configured to
15 control at least one operation of the semiconductor processor system
16 responsive to the signal.

17
18 19. The system according to claim 18 wherein the sampling
19 system is configured to provide the process fluid in a substantially static
20 state.

21
22 20. The system according to claim 19 wherein the control system
23 is configured to compare the sample of the process fluid with a
24 signature to determine at least one characteristic of the process fluid.

1 21. The system according to claim 20 wherein the control system
2 is configured to control a flow rate of the process fluid into the
3 process chamber responsive to the comparison.

4
5 22. The system according to claim 18 wherein the sensor is
6 configured to monitor turbidity of the process fluid.

7
8 23. The system according to claim 18 wherein the control system
9 is configured to control the sampling system to draw the sample of the
10 process fluid.

11
12 24. The system according to claim 18 wherein the control system
13 is configured to monitor operation of the semiconductor processor system
14 and to control the sampling system to draw the sample during defined
15 operations of the semiconductor processor system.

16
17 25. The system according to claim 18 further comprising a
18 storage device coupled with the sensor and configured to store historical
19 data corresponding to the process fluid.

20
21 26. The system according to claim 18 wherein the process
22 chamber comprises a process chamber of a chemical-mechanical polishing
23 processor.
24

1 27. A semiconductor processor system comprising:
2 a process chamber adapted to process at least one semiconductor
3 workpiece;
4 a process fluid system including:
5 a mixer configured to mix a plurality of components of a
6 process fluid;
7 a connection configured to supply the process fluid to the
8 process chamber; and
9 a sensor configured to output a signal indicative of at least
10 one of the components and the process fluid; and
11 a control system coupled with the sensor and configured to
12 control mixing of the components responsive to the signal.

13
14 28. The system according to claim 27 wherein the process fluid
15 system comprises at least one metering device configured to permit flow
16 of at least one of the components and the control system is configured
17 to control the metering device to control a flow rate of the component
18 responsive to the signal.

19
20 29. The system according to claim 27 wherein the sensor is
21 coupled with the connection.
22
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1 30. The system according to claim 27 wherein the sensor is
2 coupled with the connection and further comprising another sensor
3 coupled with a supply connection configured to supply one of the
4 components to the mixer.

5
6 31. The system according to claim 27 wherein the sensor is
7 configured to monitor turbidity of the process fluid.

8
9 32. The system according to claim 27 further comprising a
10 storage device coupled with the sensor and configured to store historical
11 data corresponding to the process fluid.

12
13 33. The system according to claim 27 wherein the process
14 chamber comprises a process chamber of a chemical-mechanical polishing
15 processor.

1 34. A semiconductor processor system comprising:
2 a process chamber adapted to process at least one semiconductor
3 workpiece using a process fluid;
4 a process fluid system coupled with the process chamber and
5 including:
6 a recirculation system configured to recirculate the process
7 fluid; and
8 a sensor coupled with the recirculation system and
9 configured to output a signal indicative of the process fluid; and
10 a control system coupled with the sensor and configured to
11 control recirculation of the process fluid using the recirculation system
12 responsive to the signal.

13
14 35. The system according to claim 34 wherein the control system
15 is configured to control the recirculation system to recirculate the
16 process fluid responsive to the process fluid being out of specification.

17
18 36. The system according to claim 34 wherein the sensor is
19 configured to monitor turbidity of the process fluid.

20
21 37. The system according to claim 34 wherein the process fluid
22 system is configured to supply process fluid to the process chamber.
23
24

1 38. The system according to claim 34 wherein the process
2 chamber comprises a process chamber of a chemical-mechanical polishing
3 processor.

4
5 39. A semiconductor processor system comprising:
6 a process chamber adapted to process at least one semiconductor
7 workpiece using a process fluid;

8 a process fluid system including:
9 a connection coupled with the process chamber and
10 configured to transport process fluid relative to the process chamber;

11 a flush system configured to flush the connection using a
12 flush fluid; and

13 a sensor coupled with the flush system and configured to
14 output a signal indicative of the flush fluid; and

15 a control system coupled with the sensor and configured to
16 control the flush system to flush the connection responsive to the signal.

17
18 40. The system according to claim 39 wherein the control system
19 is configured to control the flush system to prime the connection
20 responsive to a start-up operation of the semiconductor processor
21 system.

1 41. The system according to claim 40 wherein the flush system
2 is configured to prime the connection with flush fluid comprising process
3 fluid responsive to the start-up operation.
4

5 42. The system according to claim 40 wherein the sensor is
6 configured to monitor turbidity of the flush fluid and the control system
7 is configured to control the flush system responsive to the turbidity of
8 the flush fluid.
9

10 43. The system according to claim 39 wherein the control system
11 is configured to control the flush system to rinse the connection
12 responsive to a halt operation of the semiconductor processor system.
13

14 44. The system according to claim 43 wherein the flush system
15 is configured to rinse the connection with flush fluid comprising rinse
16 fluid responsive to the halt operation.
17

18 45. The system according to claim 43 wherein the sensor is
19 configured to monitor turbidity of the flush fluid and the control system
20 is configured to control the flush system responsive to the turbidity of
21 the flush fluid.
22

23 46. The system according to claim 39 wherein the sensor is
24 configured to monitor turbidity of the flush fluid.

1 47. The system according to claim 39 wherein the process fluid
2 system is configured to supply process fluid to the process chamber.
3

4 48. The system according to claim 39 wherein the process
5 chamber comprises a process chamber of a chemical-mechanical polishing
6 processor.
7

8 49. A semiconductor processor system comprising:

9 a process chamber adapted to process at least one semiconductor
10 workpiece using a process fluid;

11 a connection configured to transport the process fluid relative to
12 the process chamber;

13 a sensor coupled with the connection and configured to output a
14 signal indicative of accumulation of particulate matter within the
15 connection; and

16 a control system coupled with the sensor and configured to
17 monitor the accumulation responsive to the signal.
18

19 50. The system according to claim 49 wherein the connection is
20 arranged in a substantially horizontal orientation.
21

22 51. The system according to claim 50 wherein the sensor is
23 arranged to monitor accumulation in a substantially vertical orientation
24 with respect to the connection.

1 52. The system according to claim 49 further comprising a flush
2 system configured to flush the connection and wherein the control
3 system is configured to control the flush system responsive to monitoring
4 the accumulation.

5
6 53. The system according to claim 49 further comprising a
7 recirculation system configured to recirculate process fluid within the
8 connection and wherein the control system is configured to control the
9 recirculation system responsive to monitoring the accumulation.

10
11 54. The system according to claim 49 wherein the connection
12 comprises a connection configured to provide process fluid to the
13 process chamber.

14
15 55. The system according to claim 49 wherein the connection
16 comprises a drain connection configured to receive process fluid from
17 the process chamber.

18
19 56. The system according to claim 49 wherein the sensor is
20 configured to monitor turbidity of the process fluid.

21
22 57. The system according to claim 49 wherein the process
23 chamber comprises a process chamber of a chemical-mechanical polishing
24 processor.

1 58. A system configured to provide a semiconductor workpiece
2 process fluid comprising:

3 a connection configured to transport a semiconductor workpiece
4 process fluid relative to a semiconductor process chamber;

5 a sensor oriented relative to the connection and configured to
6 output a signal indicative of the semiconductor workpiece process fluid;
7 and

8 a control system coupled to receive the signal from the sensor
9 and configured to monitor the semiconductor workpiece process fluid
10 using the signal.
11

12 59. The system according to claim 58 wherein the sensor is
13 configured to output the signal indicative of turbidity of the
14 semiconductor workpiece process fluid.
15

16 60. The system according to claim 58 wherein the control system
17 is configured to compare the signal with a signature to monitor the
18 semiconductor workpiece process fluid.
19

20 61. The system according to claim 58 further comprising at least
21 one metering device configured to permit flow of a component of the
22 semiconductor workpiece process fluid, and the control system is
23 configured to control the metering device to control a flow rate of the
24 component responsive to the signal.

1 62. The system according to claim 58 wherein the process
2 chamber comprises a process chamber of a chemical-mechanical polishing
3 processor.

4
5 63. A system configured to provide a semiconductor workpiece
6 process fluid comprising:

7 a mixer configured to mix a plurality of components of a
8 semiconductor workpiece process fluid;

9 a sensor configured to output a signal indicative of at least one
10 of the components and the semiconductor workpiece process fluid; and

11 a control system coupled with the sensor and configured to
12 control mixing of the components responsive to the signal.

13
14 64. The system according to claim 63 wherein the system
15 comprises at least one metering device configured to flow one of the
16 components, and the control system is configured to control the
17 metering device to control a flow rate of the component responsive to
18 the signal.

19
20 65. The system according to claim 63 wherein the sensor is
21 configured to output the signal indicative of the semiconductor workpiece
22 process fluid, and further comprising another sensor configured to output
23 another signal indicative of one of the components.

24

1 66. The system according to claim 63 wherein the sensor is
2 configured to monitor turbidity of the semiconductor workpiece process
3 fluid.

4
5 67. The system according to claim 63 wherein the process
6 chamber comprises a process chamber of a chemical-mechanical polishing
7 processor.

8
9 68. A semiconductor workpiece processing method comprising:
10 providing a semiconductor processor system having a process
11 chamber adapted to process a semiconductor workpiece;
12 processing the semiconductor workpiece within the process chamber
13 using a process fluid;
14 monitoring the process fluid; and
15 controlling at least one operation of the semiconductor processor
16 system responsive to the monitoring.

17
18 69. The method according to claim 68 further comprising
19 providing a sample of the process fluid and the monitoring comprises
20 monitoring the sample.

1 70. The method according to claim 69 further comprising
2 providing the sample of the process fluid in a substantially static state
3 and the monitoring comprises monitoring the process fluid in the
4 substantially static state.

5
6 71. The method according to claim 69 wherein the monitoring
7 comprises comparing the sample of the process fluid with a signature.

8
9 72. The method according to claim 68 further comprising
10 flushing a connection configured to transport the process fluid and the
11 controlling comprises controlling the flushing.

12
13 73. The method according to claim 68 wherein the monitoring
14 comprises monitoring turbidity of the process fluid.

15
16 74. The method according to claim 68 further comprising
17 supplying the process fluid to the process chamber and the monitoring
18 is during the supplying.

19
20 75. The method according to claim 68 further comprising
21 draining the process fluid from the process chamber and the monitoring
22 is during the draining.

1 76. The method according to claim 68 wherein the processing
2 comprises processing using a pad, and further comprising extracting
3 process fluid from the pad during the processing and the monitoring
4 comprises monitoring the process fluid after the extracting.

5
6 77. The method according to claim 68 further comprising
7 transporting the process fluid relative to the process chamber using a
8 connection and the monitoring comprises monitoring accumulation of
9 particulate matter within the connection.

10
11 78. The method according to claim 68 further comprising:
12 receiving a start-up command of the semiconductor processor
13 system; and

14 priming a connection configured to transport the process fluid
15 using a flush fluid responsive to the receiving.

16
17 79. The method according to claim 78 wherein the priming
18 comprises priming with flush fluid comprising the process fluid.

19
20 80. The method according to claim 78 wherein the monitoring
21 comprises monitoring turbidity of the flush fluid during the priming and
22 the controlling comprises controlling the priming.

1 81. The method according to claim 68 further comprising:
2 receiving a halt command of the semiconductor processor system;
3 and

4 flushing a connection configured to transport the process fluid
5 responsive to the receiving.

6
7 82. The method according to claim 81 wherein the flushing
8 comprises flushing with flush fluid comprising a rinse fluid.

9
10 83. The method according to claim 81 wherein the monitoring
11 comprises monitoring turbidity of the flush fluid during the flushing and
12 the controlling comprises controlling the flushing.

13
14 84. The method according to claim 68 further comprising mixing
15 plural components to provide the process fluid and the controlling
16 comprises controlling the mixing.

17
18 85. The method according to claim 68 further comprising storing
19 historical data of the process fluid after the monitoring.

20
21 86. The method according to claim 68 wherein the processing
22 comprises chemical-mechanical polishing the semiconductor workpiece.

1 87. A semiconductor workpiece processing method comprising:
2 providing a semiconductor processor system adapted to process a
3 semiconductor workpiece using a process fluid;
4 providing a sample of the process fluid;
5 providing the sample of the process fluid in a substantially static
6 state;
7 monitoring the sample of the process fluid; and
8 controlling an operation of the semiconductor processor system
9 responsive to the monitoring.
10

11 88. The method according to claim 87 wherein the monitoring
12 comprises monitoring the turbidity of the sample of the process fluid.
13

14 89. The method according to claim 87 wherein the monitoring
15 comprises monitoring differential turbidity of the sample of the process
16 fluid.
17

18 90. The method according to claim 89 wherein the monitoring
19 comprises monitoring differential turbidity with respect to different
20 moments in time.
21

22 91. The method according to claim 87 wherein the monitoring
23 comprises comparing the sample of the process fluid with a signature.
24

1 92. The method according to claim 87 wherein the controlling
2 comprises controlling a flush system to at least one of prime and rinse
3 a connection configured to transport the process fluid.

4
5 93. The method according to claim 87 wherein the controlling
6 comprises controlling a recirculation system to recirculate the process
7 fluid.

8
9 94. The method according to claim 87 further comprising
10 monitoring an operation of the semiconductor processor system and the
11 providing the sample comprises providing the sample during defined
12 operations of the semiconductor processor system.

13
14 95. The method according to claim 87 further comprising storing
15 historical data of the process fluid after the monitoring.

16
17 96. A method of preparing semiconductor workpiece process
18 fluid comprising:

19 providing plural process fluid components;

20 mixing the process fluid components to form a semiconductor
21 workpiece process fluid;

22 monitoring at least one of the process fluid components and the
23 process fluid; and

24 controlling the mixing responsive to the monitoring.

1 97. The method according to claim 96 wherein the monitoring
2 comprises monitoring the process fluid.

3
4 98. The method according to claim 96 wherein the monitoring
5 comprises monitoring both process fluid components.

6
7 99. The method according to claim 96 wherein the monitoring
8 comprises monitoring both process fluid components and the process
9 fluid.

10
11 100. The method according to claim 96 wherein the monitoring
12 comprises monitoring turbidity.

13
14 101. The method according to claim 96 wherein the controlling
15 comprises adjusting flow rates of the process fluid components.

16
17 102. The method according to claim 96 further comprising storing
18 historical data of at least one of the process fluid components and the
19 process fluid after the monitoring.

1 103. A semiconductor workpiece processing method comprising:
2 providing a semiconductor processor system adapted to process a
3 semiconductor workpiece using a process fluid;
4 transporting the process fluid relative to the semiconductor
5 processor system;
6 monitoring the process fluid; and
7 recirculating the process fluid after the monitoring.
8

9 104. The method according to claim 103 wherein the monitoring
10 comprises monitoring turbidity of the process fluid.
11

12 105. The method according to claim 103 further comprising
13 supplying the process fluid to a process chamber of the semiconductor
14 processor system after the recirculating.
15

16 106. The method according to claim 103 further comprising
17 controlling the recirculating responsive to the monitoring.
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1 107. A semiconductor workpiece processing method comprising:
2 providing a semiconductor processor system adapted to process a
3 semiconductor workpiece using a process fluid;
4 transporting the process fluid relative to the semiconductor
5 processor system using a connection;
6 flushing the connection using a flush fluid; and
7 monitoring the flush fluid during the flushing.

8
9 108. The method according to claim 107 wherein the flushing
10 comprises at least one of priming and rinsing the connection.

11
12 109. The method according to claim 107 wherein the monitoring
13 comprises monitoring turbidity of the flush fluid.

14
15 110. The method according to claim 107 further comprising
16 controlling the flushing responsive to the monitoring.

17
18 111. The method according to claim 107 further comprising
19 supplying the process fluid to a process chamber of the semiconductor
20 processor system after the flushing.

21
22 112. The method according to claim 107 further comprising
23 receiving a start-up command of the semiconductor processor system and
24 the flushing comprises priming responsive to the receiving.

1 113. The method according to claim 112 wherein the priming
2 comprises priming with flush fluid comprising the process fluid.
3

4 114. The method according to claim 112 further comprising:
5 monitoring turbidity of the flush fluid; and
6 controlling the flushing responsive to the monitoring.
7

8 115. The method according to claim 107 further comprising
9 receiving a halt command of the semiconductor processor system and
10 the flushing comprises rinsing responsive to the receiving.
11

12 116. The method according to claim 115 wherein the flushing
13 comprises rinsing with flush fluid comprising a rinse fluid.
14

15 117. The method according to claim 115 further comprising:
16 monitoring turbidity of the flush fluid; and
17 controlling the flushing responsive to the monitoring.
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1 118. A semiconductor workpiece processing method comprising:
2 providing a semiconductor processor system adapted to process a
3 semiconductor workpiece using a process fluid;
4 transporting the process fluid relative to the semiconductor
5 processor system using a connection;
6 monitoring accumulation of particulate matter within the
7 connection; and
8 controlling at least one operation of the semiconductor processor
9 system responsive to the monitoring.

10
11 119. The method according to claim 118 wherein the transporting
12 comprises transporting using a substantially horizontal connection.

13
14 120. The method according to claim 119 wherein the monitoring
15 comprises monitoring in a substantially vertical direction.

16
17 121. The method according to claim 118 wherein the monitoring
18 comprises monitoring turbidity.

19
20 122. The method according to claim 118 wherein the controlling
21 comprises controlling a flushing operation of the connection responsive
22 to the monitoring.

1 123. The method according to claim 118 wherein the controlling
2 comprises controlling a recirculating operation of the connection
3 responsive to the monitoring.

4
5 124. The method according to claim 118 wherein the transporting
6 comprises supplying process fluid to a process chamber of the
7 semiconductor processor system.

8
9 125. The method according to claim 118 wherein the transporting
10 comprises draining process fluid from a process chamber of the
11 semiconductor processor system.

12
13 126. A method of delivering semiconductor workpiece process
14 fluid to a semiconductor processor comprising:

15 providing semiconductor workpiece process fluid;

16 transporting the semiconductor workpiece process fluid relative to
17 a semiconductor processor; and

18 monitoring the semiconductor workpiece process fluid.

19
20 127. The method according to claim 126 wherein the monitoring
21 comprises monitoring turbidity of the semiconductor workpiece process
22 fluid.

1 128. The method according to claim 126 wherein the monitoring
2 comprises comparing the semiconductor workpiece process fluid with a
3 signature.

4
5 129. The method according to claim 126 wherein the providing
6 comprises mixing a plurality of components of the semiconductor
7 workpiece process fluid, and further comprising controlling the mixing
8 responsive to the monitoring.